



WIR SCHAFFEN WISSEN – HEUTE FÜR MORGEN

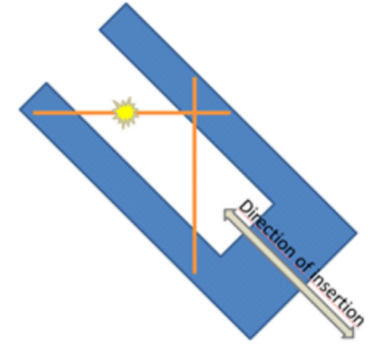
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Wire-Scanners (WS) with Sub-Micrometer Resolution: Developments and Measurements

Overview

- *Motivations and Goals*
- *Nano-fabricated WS at PSI and FERMI: first developments*
- *Nano-fabrication of free-standing sub- μm WS at PSI and FERMI*
- *Free-standing sub- μm WS: experimental test at SwissFEL*
- *Conclusions and Outlook*

Motivations and Goals



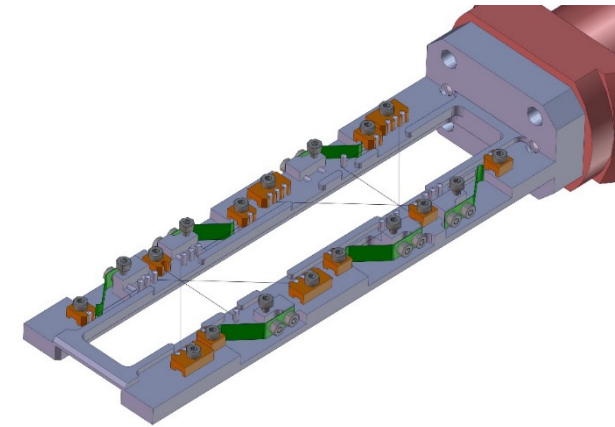
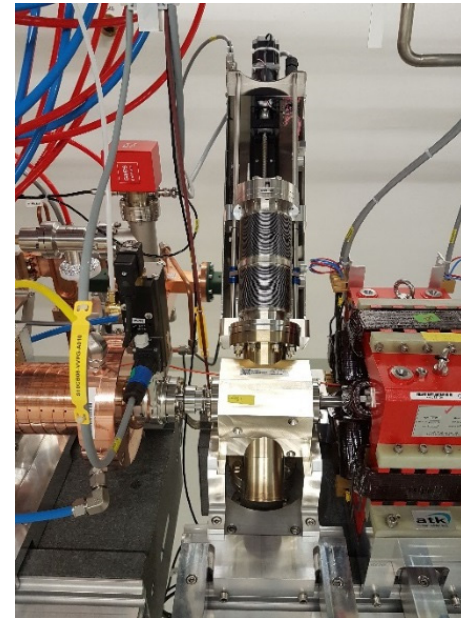
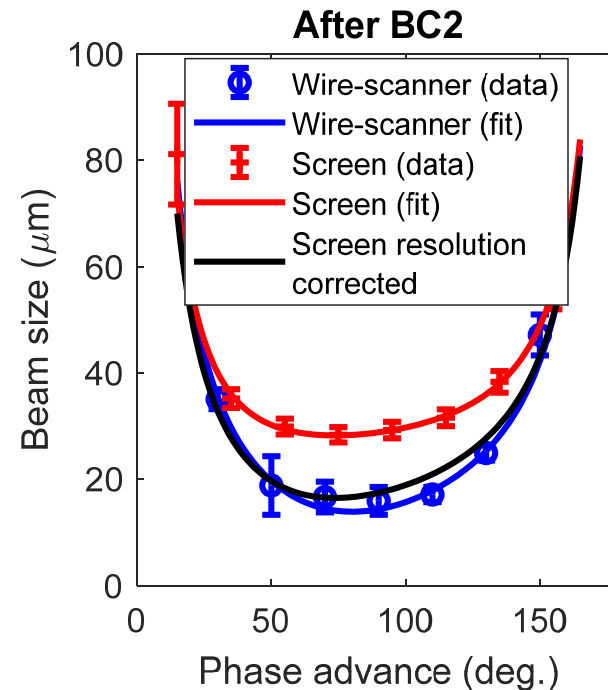
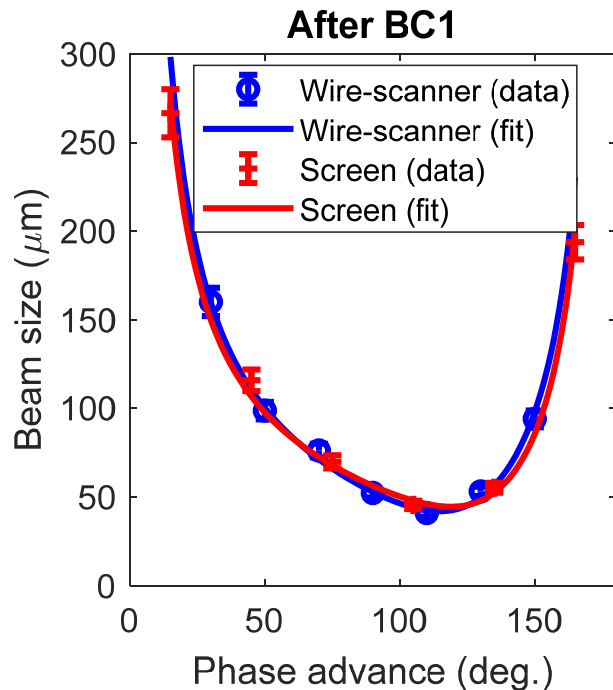
- Diagnostics with sub- μm resolution needed for:
 - Low-charge and low emittance FEL operations
 - Novel laser and plasma driven accelerator
- WS top ranked beam profile monitors → spatial resolution and minimal invasivity
- Conventional WS (cylindrical metallic wires stretched onto a fork): spatial resolution limit $\sim 1\mu\text{m}$ (rms)
- Higher WS spatial resolution $\longleftrightarrow$ thinner wire $\longleftrightarrow$ smaller number of perturbed electrons $\longleftrightarrow$ minimal beam invasivity and higher lasing transparency
- New techniques to fabricate WS with resolution beyond the $1\mu\text{m}$ (rms) limit
 - Nano-lithography (integration wire+fork in unique structure)
- Nowadays, free-standing WS independently nano-fabricated at PSI and FERMI and tested at SwissFEL:
 - sub- μm spatial resolution ($\sim 250\text{ nm}$)
 - beam clearance $\sim 2\text{mm}$
- Near future, nano-fabricated free-standing WS with sub- μm resolution and beam clearance $\sim 10\text{mm}$
- Final goal, free-standing sub- μm wires (X,Y scan) integrated into a fork as standard WS solution for a FEL.

Conventional WS: resolution and invasivity constraints (1/2)

SwissFEL WS:

- Conventional WS design (metallic wire stretched onto a fork)
- ~20 WS installed all along the machine for beam profile monitoring and emittance measurements
- Fork equipped with 2 pairs of wires (5 μm W and 12.5 μm Al(99):Si(1) wires)
- SwissFEL, WS-relevant parameters: 200/10 pC, 0.300-5.8 GeV, beam-size 5-500 μm (rms)
- Geometrical resolution (5 μm W wire): 1.25 μm

Beam charge 10 pC, beam energy after BC1 ~300MeV, BC2~5.5 GeV



Emittance measurements at SwissFEL: WS vs YAG screen,
in this conference, Ph. Dijkstal talk
THB03 *Emittance Measurements and Minimization at SwissFEL*

Conventional WS: resolution and invasivity constraints (2/2)

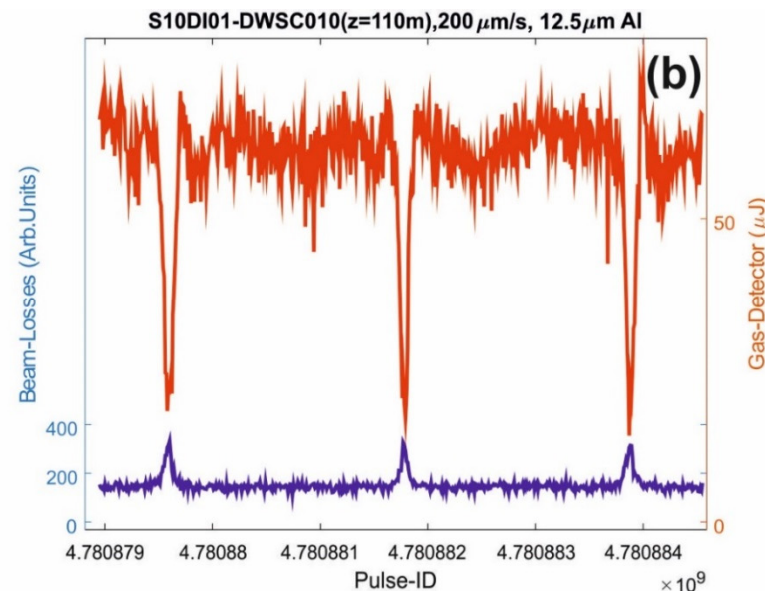
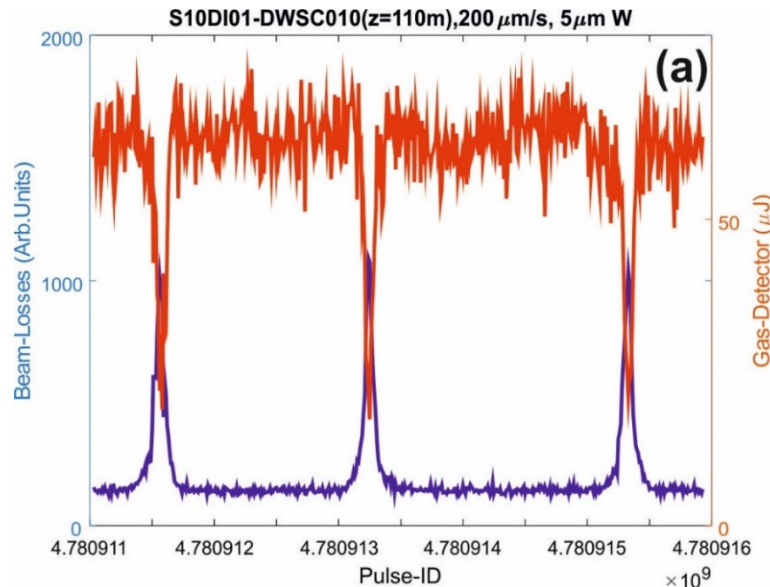
Simultaneous WS and laser pulse energy measurements with gas detector (*):

Scan electron beam with 5 μ m W wire and 12.5 μ m Al(99):Si(1) wire and, in parallel, measure laser pulse energy

Al(99):Si(1) vs W wire $\rightarrow$ beam-loss reduction by a factor 3-4 (beneficial to machine protection)

Al(99):Si(1) vs W wire $\rightarrow$ despite lower density and atomic number, larger impact surface detrimental to lasing transparency

Higher WS geometrical resolution of the wire $\rightarrow$ better wire transparency to the lasing



Energy (dE) radiated by single electron with energy E in a thickness dX of matter with radiation length L_R

$$\frac{dE}{E} = \frac{dX}{L_R}$$

$$\frac{\Delta E_W}{\Delta E_{Al}} = R_{W/Al} \frac{X_W}{L_W} \frac{L_{Al}}{X_{Al}} = 4.1$$

$$R_{W/Al} = 0.4$$

$$L_{Al} = 8.9 \text{ cm}$$

$$L_W = 0.35 \text{ cm}$$

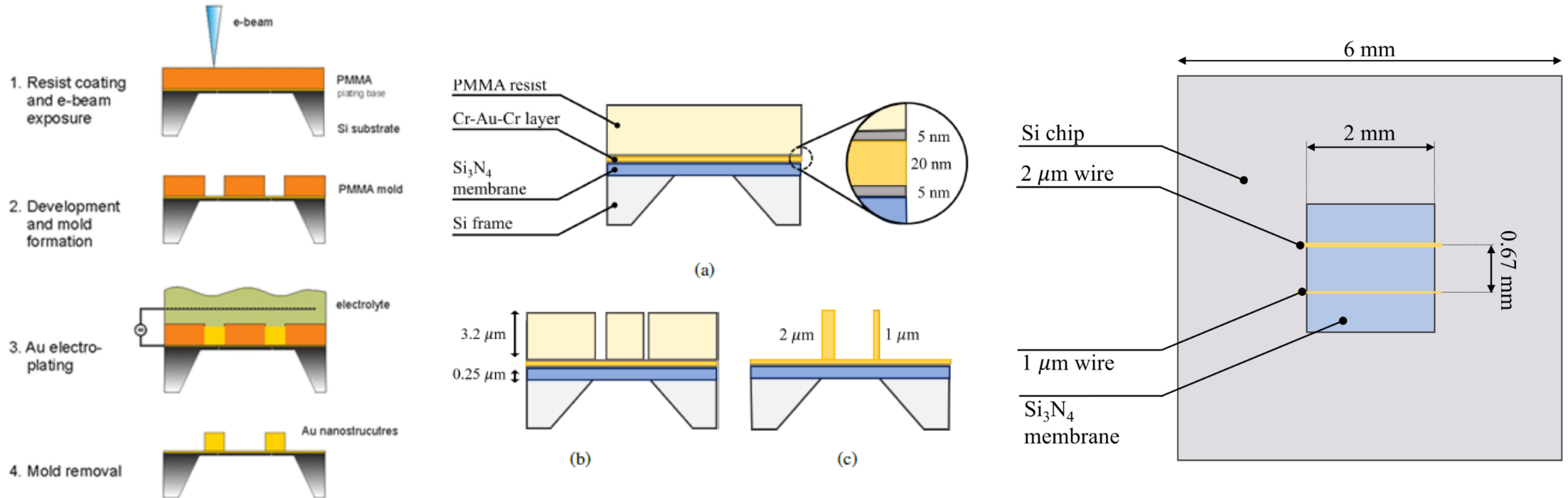
Beam-synchronous measurements of laser pulse energy (Gas-Detector) and e-beam profile (WS):

(a) 5 μ m W wire;

(b) 12.5 μ m Al(99):Si(1) wire.

Bunch charge ~ 200 pC, beam energy ~ 300 MeV at the WS location, 2.6 GeV at the undulator beamline, photon energy 2.488 keV (wavelength=4.983Å) .

(*) P. Juranic, et al., *SwissFEL Aramis beamline photon diagnostics*, J. Synchrotron Rad. (2018). 25, 1238-1248.



WS nano-fabrication at Laboratory for Micro- and Nanotechnology (LMN, PSI):

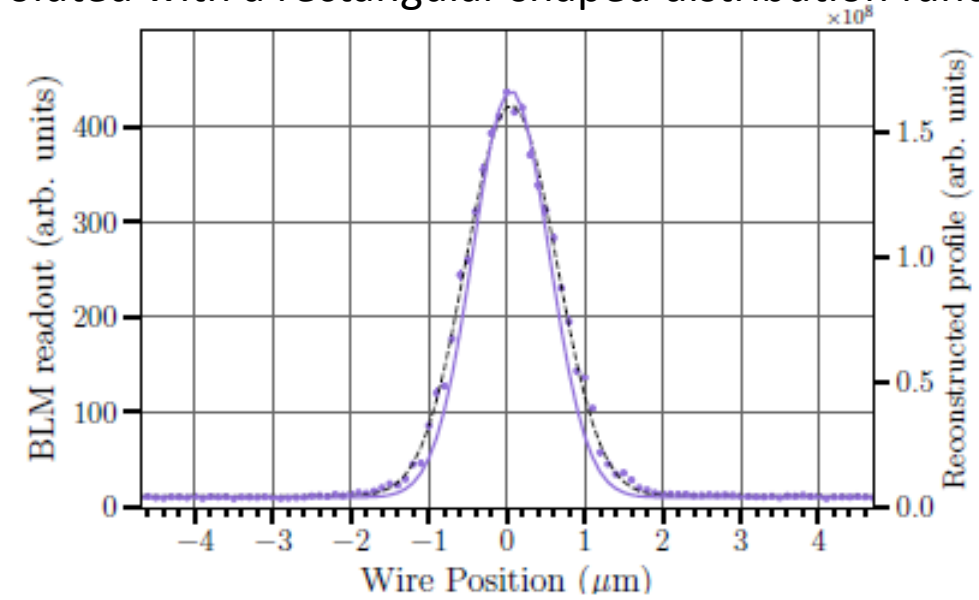
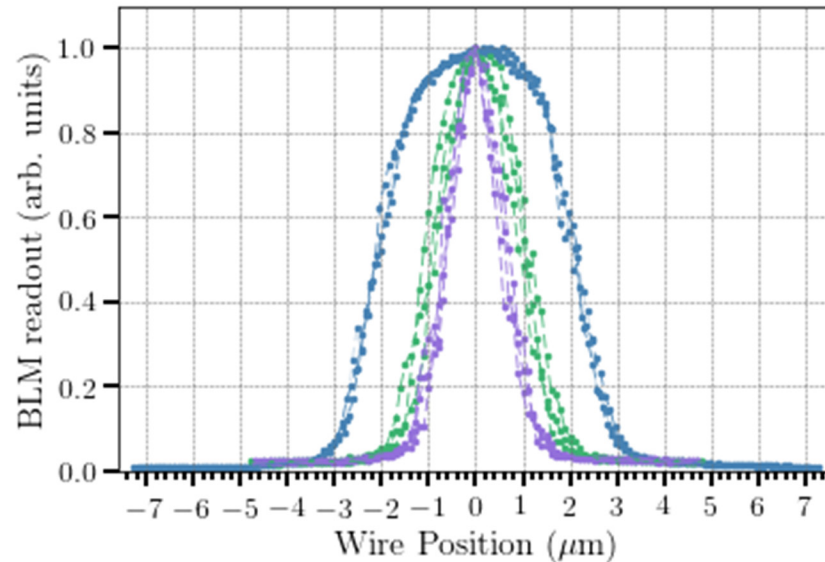
(a) Si_3N_4 membrane + Cr-Au-Cr coating + PMMA resist spin-coating

(b) e-beam lithography of PMMA to write parallel stripes (isopropanol+water treatment to develop exposed resist)

(c) Developed membrane trenches filled with Au by electroplating (PMMA resist removed by oxygen-plasma)

Sub- μm WS on-a-membrane: e-beam test at SwissFEL (*)

- Low charge and emittance machine setting: 330MeV, <1pC, emittance ~ 50 nm, vertical beam size ~ 500 nm
- Beam profile analysis: fit with a Gaussian profile convoluted with a rectangular shaped distribution function



	5 μm W	2 μm Au	1 μm Au
Resolution (nm)	1250	600	300
σ_{rms} (nm)	1967 ± 16	890 ± 2	449 ± 32
σ_y (nm)	462 ± 11	491 ± 4	491 ± 5

(*) S. Borrelli, G. L. Orlandi, M. Bednarzik, C. David, E. Ferrari, V. A. Guzenko, C. Ozkan-Loch, E. Prat, R. Ischebeck, *Generation and Measurement of Sub-Micrometer Relativistic Electron Beams*, Communications Physics-Nature, 1, 52 (2018).



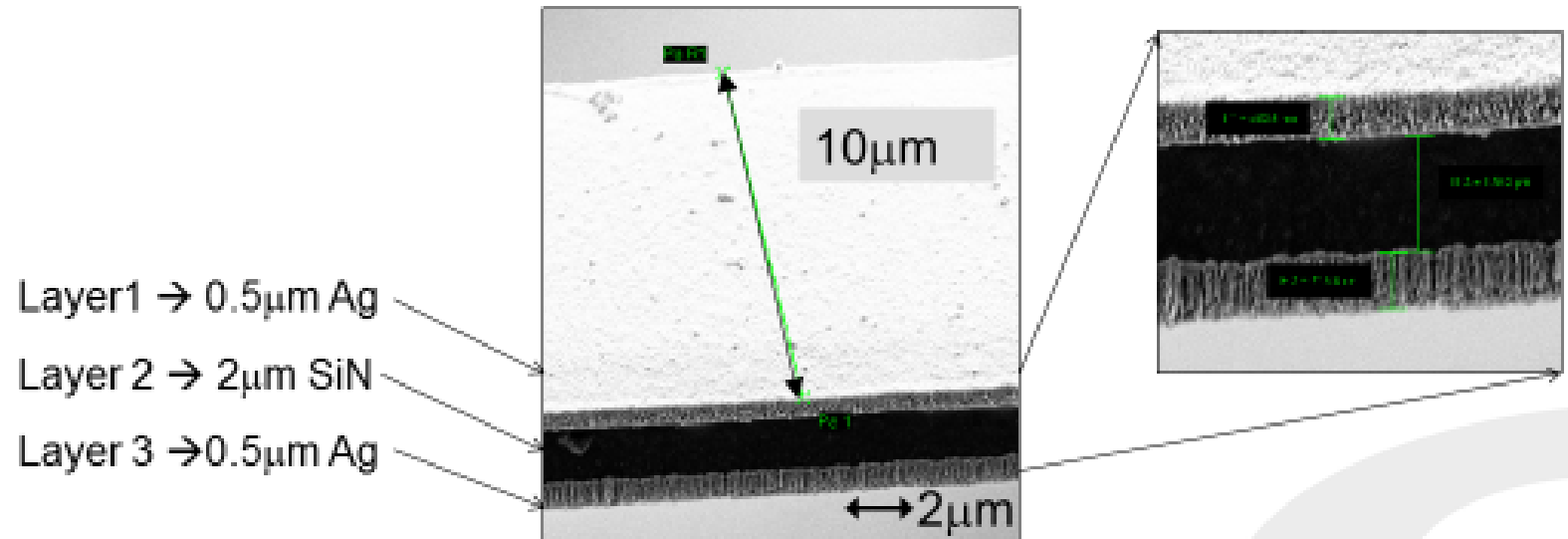
NF WIRE STRUCTURE

Our device has 3 layers:

SiN NF wires with size $2\mu\text{m} \times 10\mu\text{m}$ (thickness x width) + Ag coating on both sides.

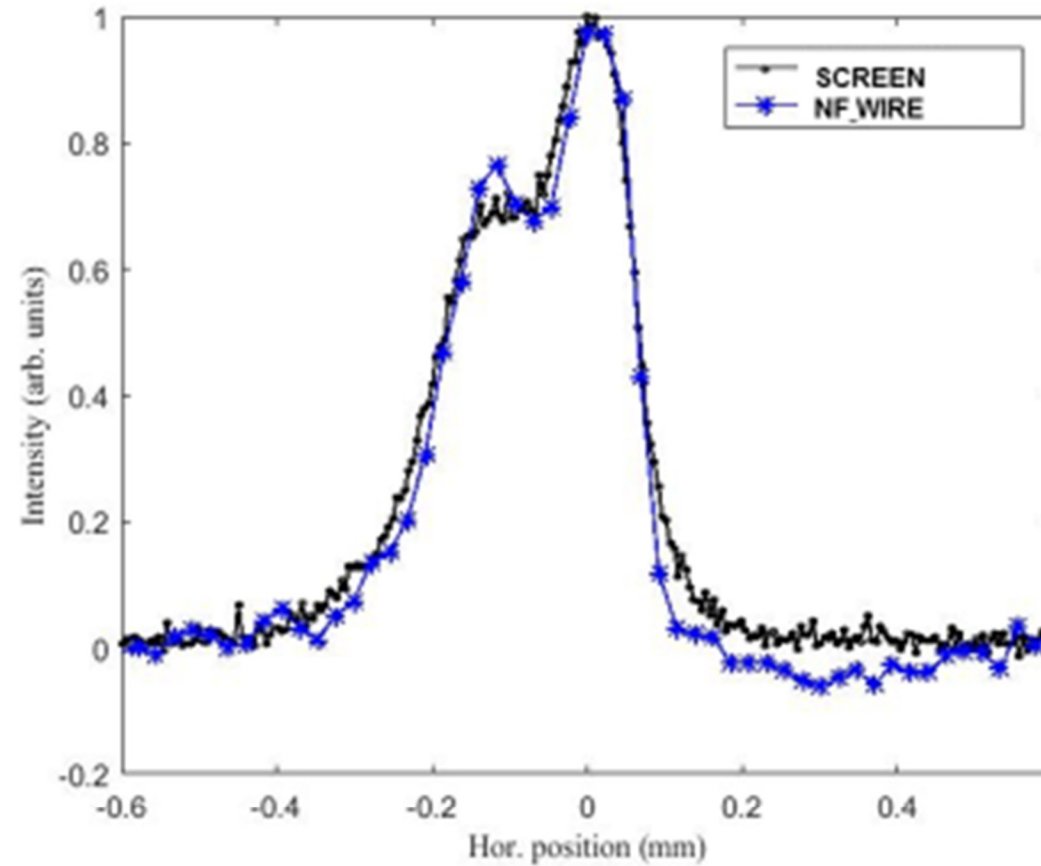
Two side coating balance stress and improve signal.

**Free-standing WS nano-fabricated
by IOM-CNR and tested at FERMI:
geometrical resolution $2.9\mu\text{m}$**



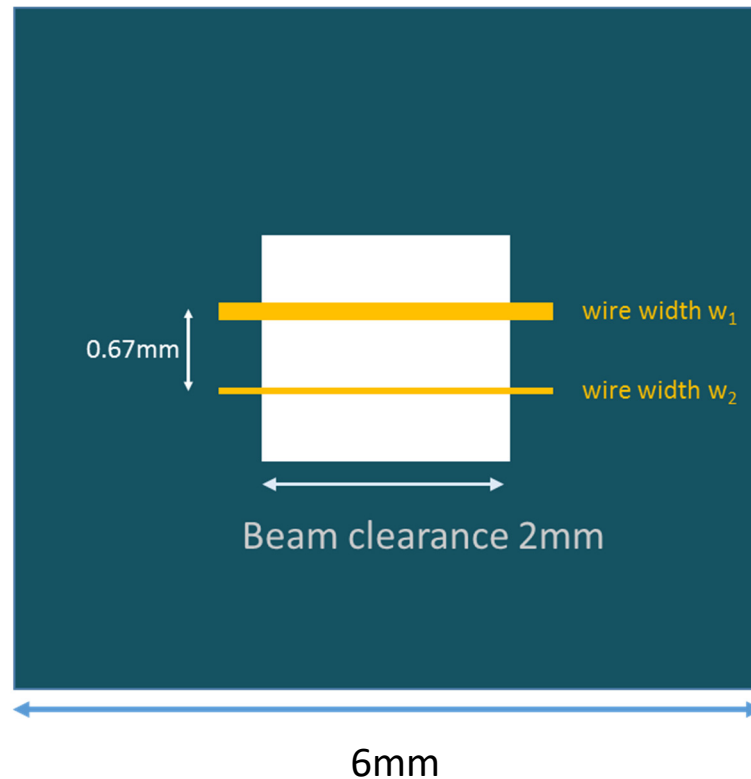
(*) M. Veronese, S. Grulja, G. Penco, M. Ferianis, L. Froehlich, S. Dal Zilio, S. Greco, M. Lazzarino,
*A nanofabricated wirescanner with free standing
wires: Design, fabrication and experimental results,*
NIM A, 891, 32-36 (2018).

NF WIRE vs HIGH RESOLUTION SCREEN

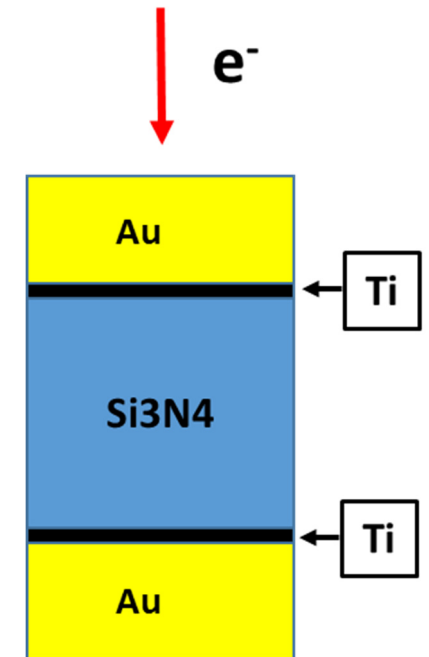
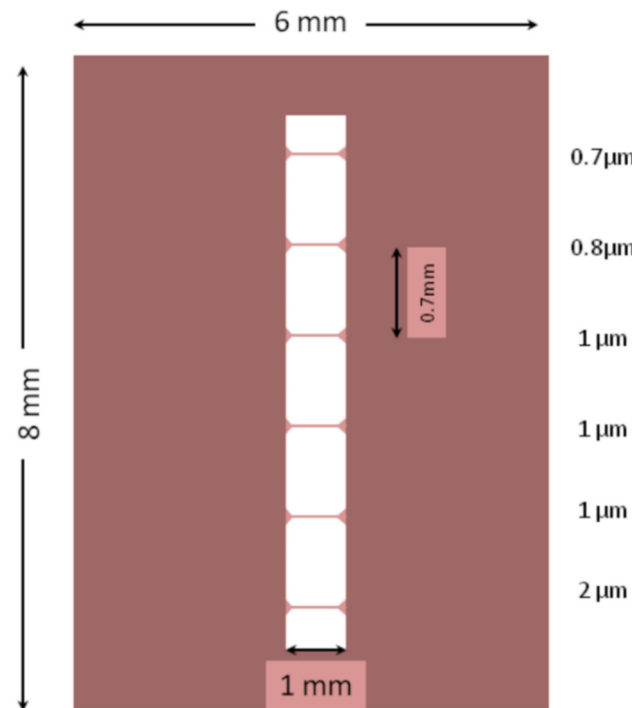


PSI and FERMI nano-fabricated free-standing WS

PSI WS chip: bulk Au stripe; width 800nm and 500nm; thickness $\sim 2\mu\text{m}$



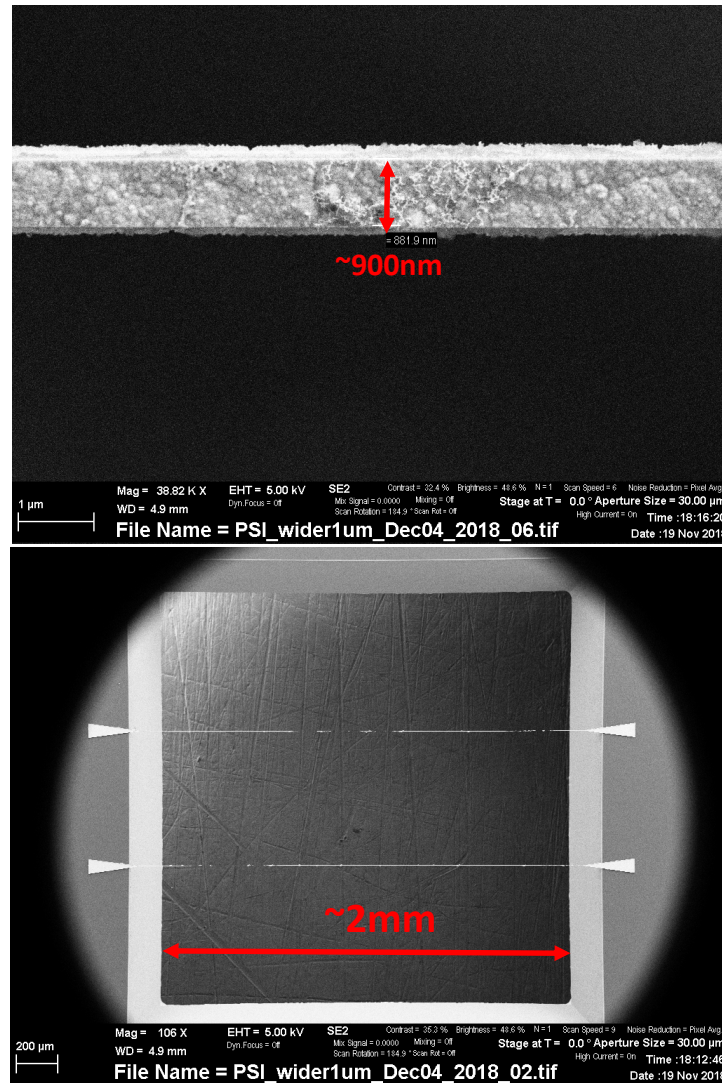
FERMI WS chip: sandwich Au/Si₃N₄/Au; thickness $\sim 3\mu\text{m}$ [Au($1\mu\text{m}$), Si₃N₄($2\mu\text{m}$), Ti(20nm)]



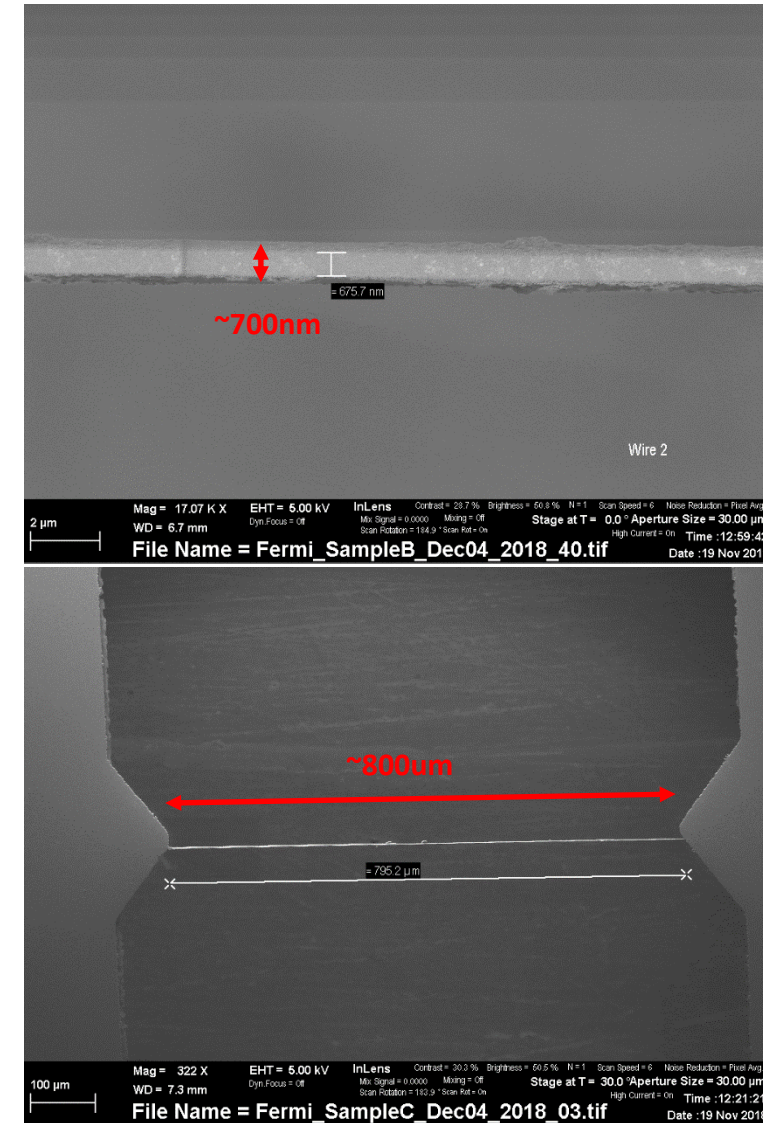
Bulk Au vs sandwich Au/Si₃N₄/Au:

- Higher signal-to-noise ratio (see WS measurement slide)
- Possible minor mechanical stability when increasing the beam clearance

SEM images of the nano-fabricated WS structures

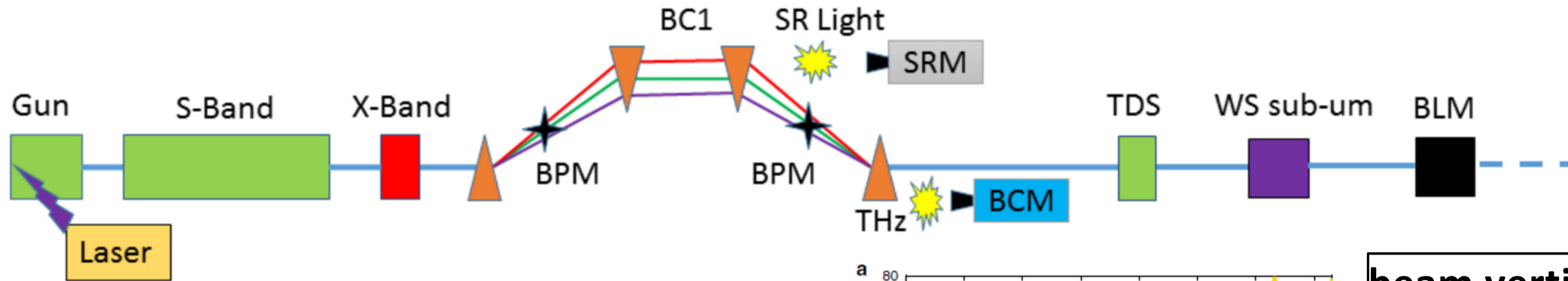


PSI WS nano-fabrication,
Laboratory for Micro- and Nanotechnology, LMN, PSI



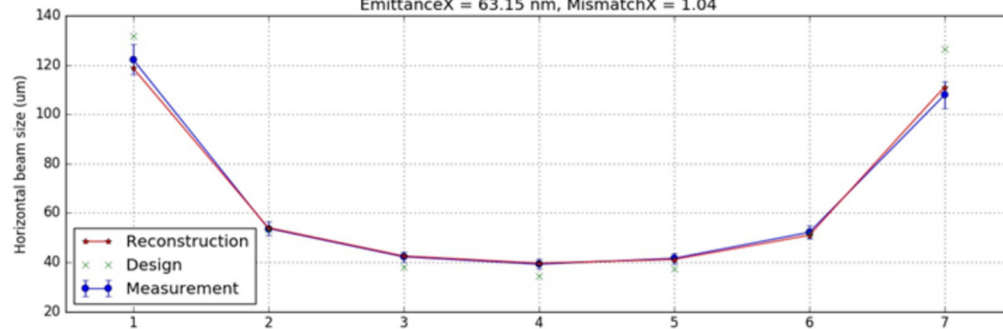
FERMI WSC nano-fabrication,
IOM-CNR, Trieste, Italy

Experimental set-up at SwissFEL

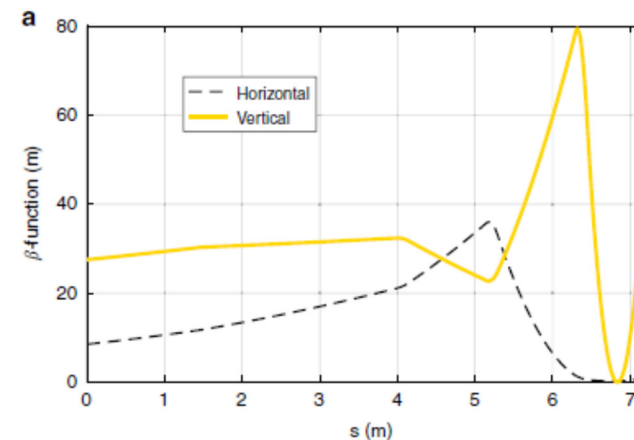
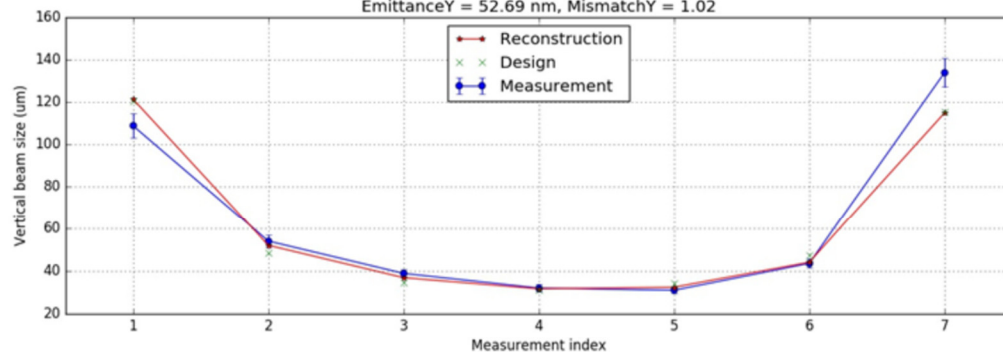


Laser Heater: energy 1.40e+02 MeV

EmittanceX = 63.15 nm, MismatchX = 1.04



EmittanceY = 52.69 nm, MismatchY = 1.02



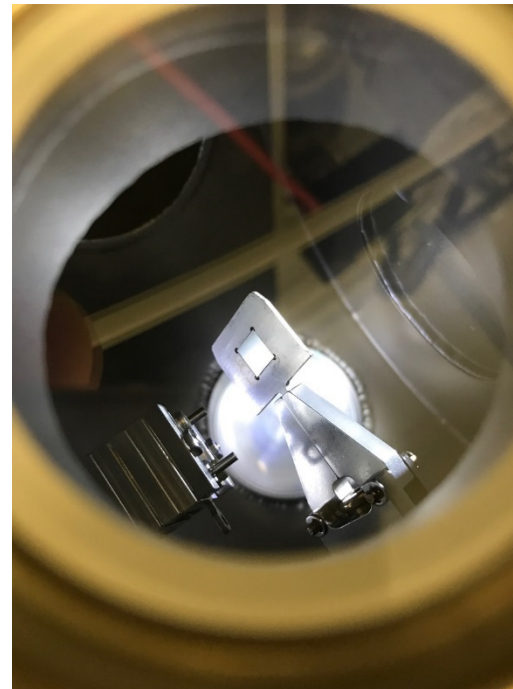
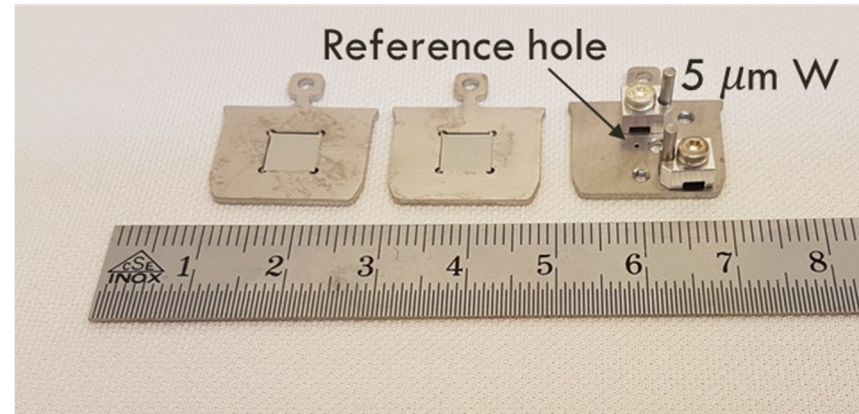
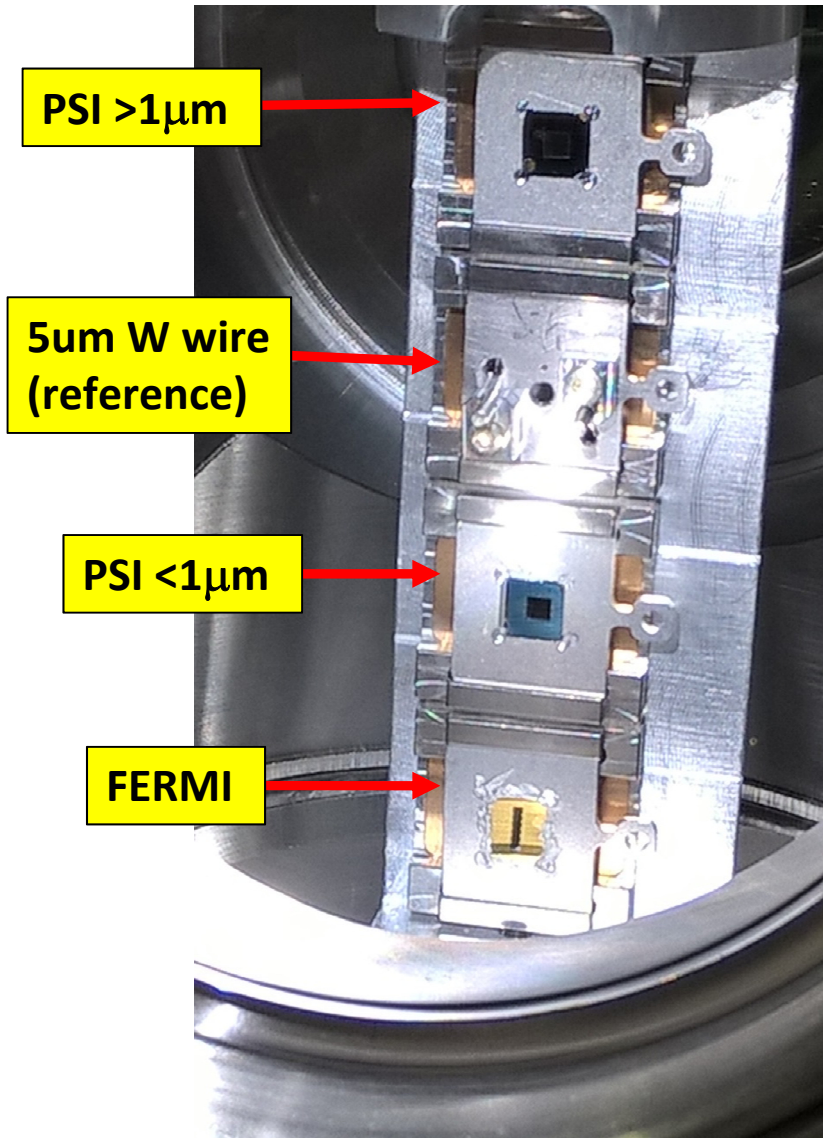
β_x, β_y evolution between BC1 and WS sub- μ m

beam vertical size at the WS position: ~500nm

Table 2 Beam parameters

E (MeV)	Q (pC)	β -functions		Emittances	
		β_x (m)	β_y (mm)	$\epsilon_{n,x}$ (nm)	$\epsilon_{n,y}$ (nm)
300	<1	0.273	2.61	42	53

Sub-um WS set-up in the sample holder of the “ACHIP” vacuum-chamber



WS chips mounted on a 4-slot sample holder.

ACHIP vacuum chamber equipped with:

- Load-lock pre-vacuum chamber
- UHV feed-through
- Stepper motor
- Encoder (0.1 μ m resolution)

Only vertical WS measurements are possible!

Free-standing sub- μm WS: experimental test at SwissFEL (*)

WS type	stripe width(nm)	geom. res.(nm)	beam size (nm, Dec 2018)	beam size (nm, Mar 2019)
PSI-WS	800	230	488 $\pm$ 20	434 $\pm$ 7
FERMI-WS	900	260	477 $\pm$ 70	443 $\pm$ 33

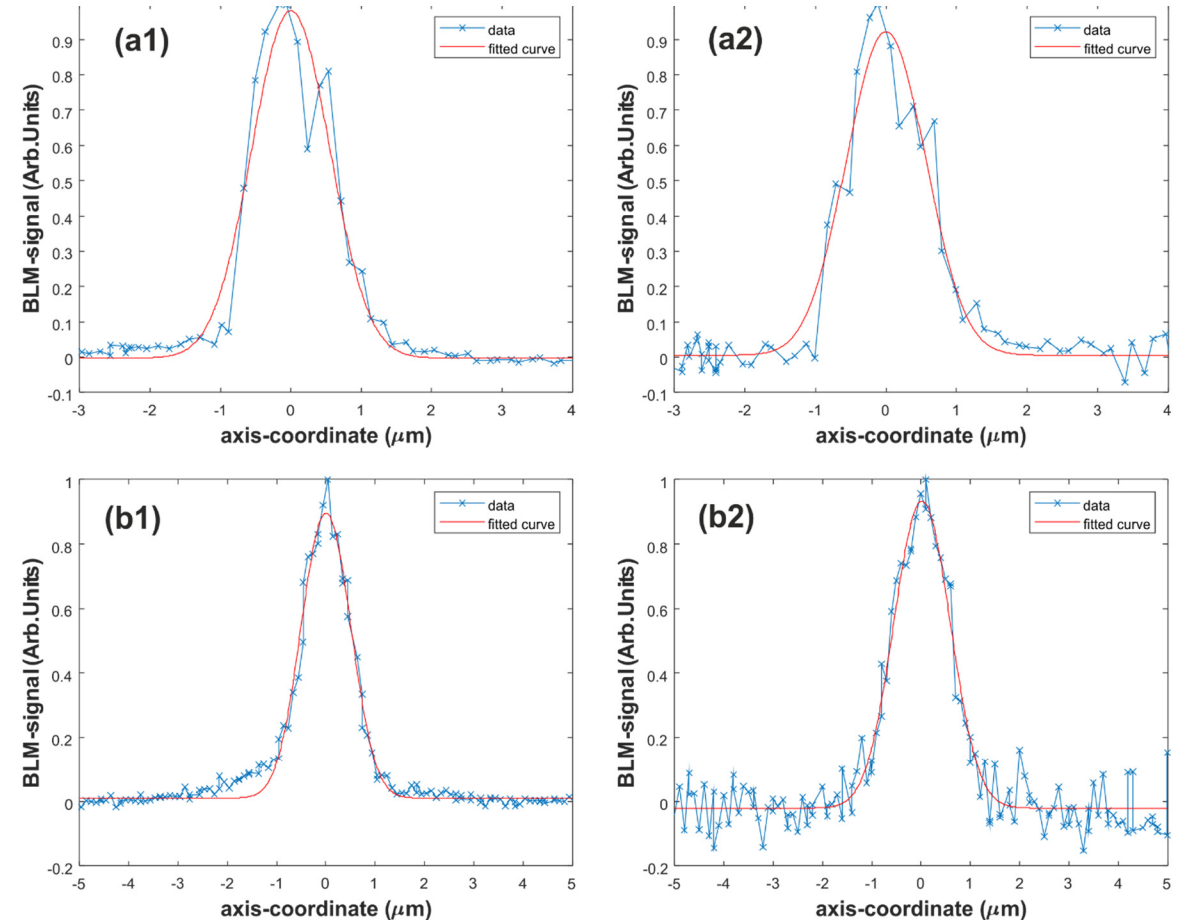
Beam profiles acquired with PSI (1) and FERMI (2) WS in two different measurement sessions (a, b):

- low-charge (<1pC)
- low emittance ($\varepsilon_y \sim 55 \text{ nm}$) $\rightarrow$ beam size $\sim 500 \text{ nm}$
- beam energy $\sim 300 \text{ MeV}$

Error-function-fit: convolution of Gaussian distribution with rectangular shaped distribution with a width w :

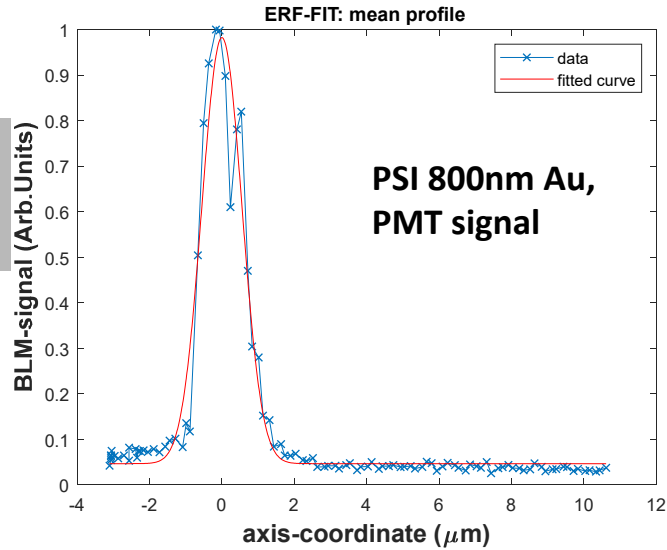
$$\text{erf-fit}(x) = a \times [\text{erf}([x - c + w/2]/\sqrt{2}/\sigma) + \text{erf}([x - c - w/2]/\sqrt{2}/\sigma)] + b,$$

A heat-loading resilience test: no damage observed in WS structures at 200 pC



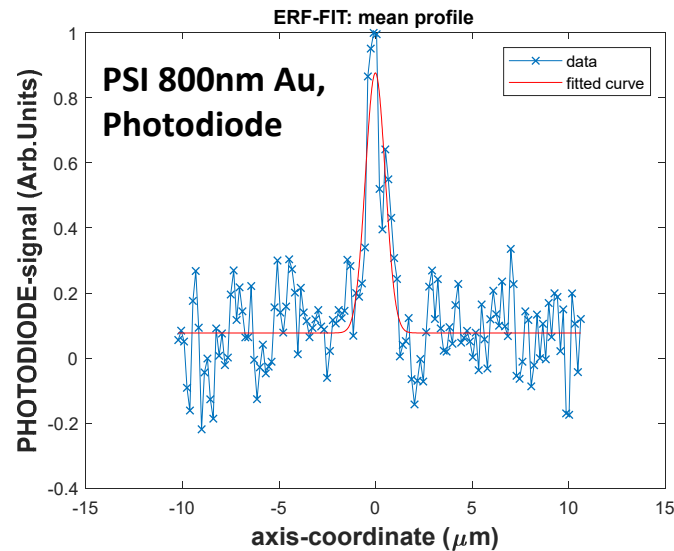
(*) G.L. Orlandi et al., *Nanofabricated free-standing wire scanners with sub-micrometer resolution*, submitted for publication

Satellite measurements: PMT vs photo-diode WS profile reconstruction

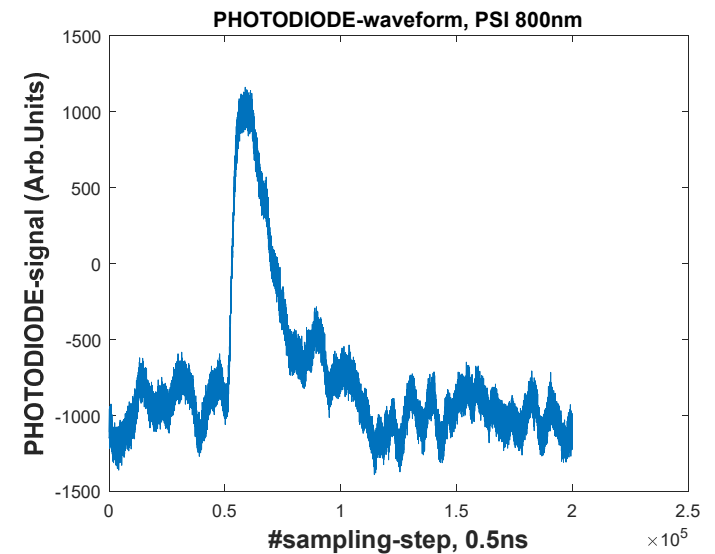
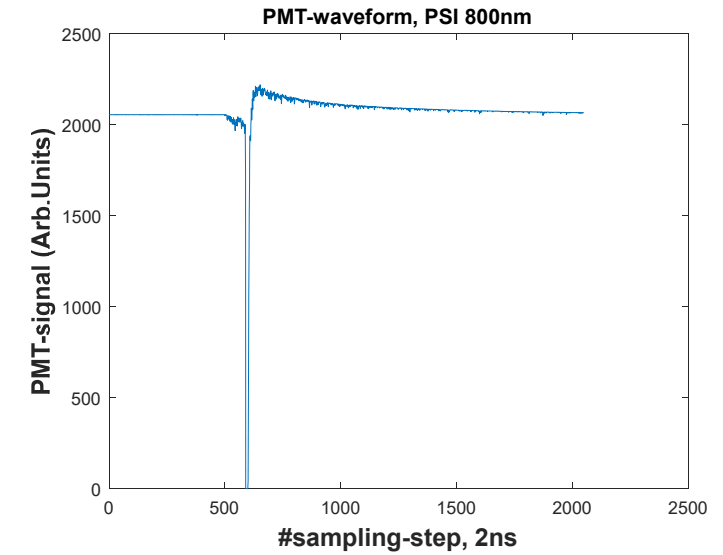


Tests of new detection solutions of the beam-loss signal: photo-diode vs PMT

WIRE	FIT	SIGMA (nm)	BEAM-LOSS-DETECTOR
PSI 800nm	ERF fit	488+/-20	PMT
FERMI 900nm	ERF fit	477+/-70	PMT
PSI 800nm	ERF fit	498+/-134	Photodiode



$$[S/N_Ratio(PMT)]/[S/N_Ratio(PHOTODIODE)] \sim 10$$



Conclusions and Outlook

- Innovative free-standing WS structure - nano-fabricated at PSI and FERMI-IOM-CNR - with unprecedented sub-micrometer geometrical resolution ($\sim 250\text{nm}$)
- Successful and statistically consistent experimental tests at SwissFEL of free-standing WS at low charge ($< 1\text{pC}$, $\sigma \sim 500\text{nm}$, 300MeV) and high charge (200 pC , heat-loading resilience test)
- Fruitful collaboration between FERMI-IOM-CNR and PSI: possible synergy in nano-fabrication and joint experimental activities
- Long terms goal:
 - Make nano-fabricated WS with sub-micrometer resolution a standard diagnostics solution for a FEL:
 - Increase the WS beam clearance from the present 2mm up to 10mm , at least.
 - Nano-fabricated WS fork with integrated free-standing stripe pair for X,Y scanning
 - Mechanical stability studies: bulk metal or metal-silicon-nitride sandwich stripe?
 - Beam-loss signal-to-noise ratio: optimize ratio thickness-to-width of the stripe (from 1 up)

Thank you for your attention

